

EPC Announces EPC2378 25 V, 410 $\mu\Omega$ eGaN® in Mass Production for High-Density DC-DC Conversion

Combining ultra-low RDS (on) and fast switching for compact power designs

EL SEGUNDO, CA, UNITED STATES, June 8, 2026 /EINPresswire.com/ -- [Efficient Power Conversion \(EPC\)](#), a leader in enhancement-mode gallium nitride (eGaN®) power devices, today announced that its new [EPC2378](#) 25 V eGaN power transistor has entered mass production, enabling high-density power system designers to achieve higher efficiency, faster switching and greater power density in demanding DC-DC conversion applications. EPC2378 is optimized for synchronous rectifier applications on the secondary side of a 48V-8 or 5V LLC converter. In addition to the best-in-class 410 $\mu\Omega$ typ. RDS(on), the devices have an industry leading low RDS(on) x QG figure of merit that enables higher frequency and higher efficiency operation. These capabilities are of particular value in fast growth markets such as AI infrastructure, data centers, telecom, industrial systems and advanced computing platforms.

The EPC2378 can handle continuous drain currents of up to 101 A, making it ideal for high current, low voltage power designs. Packaged in a compact 3.3 mm x 3.3 mm PQFN footprint with a backside thermal pad, the device is optimized for high power-density applications demanding superior thermal management and maximum efficiency.

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EPC2378 Now in mass production



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Alex Lidow, CEO and Co-Founder, EPC

losses,” said Alex Lidow, CEO and co-founder of EPC.

The EPC2378 showcases the power of eGaN technology by delivering very low conduction losses with excellent switching performance, enabling power designers to achieve higher efficiency, higher power density, and more compact system designs in demanding applications such as AI infrastructures.

To accelerate development and simplify evaluation, EPC will also introduce the EPC90185 development board, a dedicated platform designed to demonstrate the full capabilities of the EPC2378. The board integrates two EPC2378 transistors with a half-bridge gate driver, a dead-

time generation circuit, input capacitors, sense points and high current connectors, enabling engineers to rapidly evaluate performance in real-world applications.

The EPC2378 is now in mass production and available for ordering through EPC’s global distribution channels and direct sales, enabling customers to scale designs for data center power supplies, synchronous rectification stages, motor drives, and other high-density power conversion use cases.

Price and Availability

The EPC2378 eGaN FET is priced at 3K units per reel at \$2.40 each. The EPC90185 development board is priced at \$226/each.

Both the EPC2378 and EPC90185 demonstration board will be available for delivery from Digi-Key at <https://www.digikey.com/en/supplier-centers/epc> and Mouser at <https://eu.mouser.com/manufacture/epc/> by the end of June.

Designers interested in replacing their silicon MOSFETs with a GaN solution can use the EPC GaN Power Bench’s cross-reference tool to find a suggested replacement based on their unique operating conditions. The cross-reference tool can be found at: [/epc/design-support/part-cross-reference-search](https://epc.com/design-support/part-cross-reference-search)

About EPC

EPC is the leader in enhancement mode gallium nitride (eGaN®) based power management. Founded in 2007 by experts in power electronics, semiconductors, and business management, the company leverages cutting-edge technology to advance the field of power electronics through the development and commercialization of GaN-based power devices. eGaN FETs and integrated circuits provide performance many times greater than the best silicon power MOSFETs in applications such as DC-DC converters, remote sensing technology (lidar), motor drives for eMobility, robotics, and drones, and satellites.

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Press contact: Efficient Power Conversion: Maurizio Di Paolo Emilio email:

maurizio.dipaoloemilio@epc-co.com

Maurizio Di Paolo Emilio

Efficient Power Conversion

maurizio.dipaoloemilio@epc-co.com

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